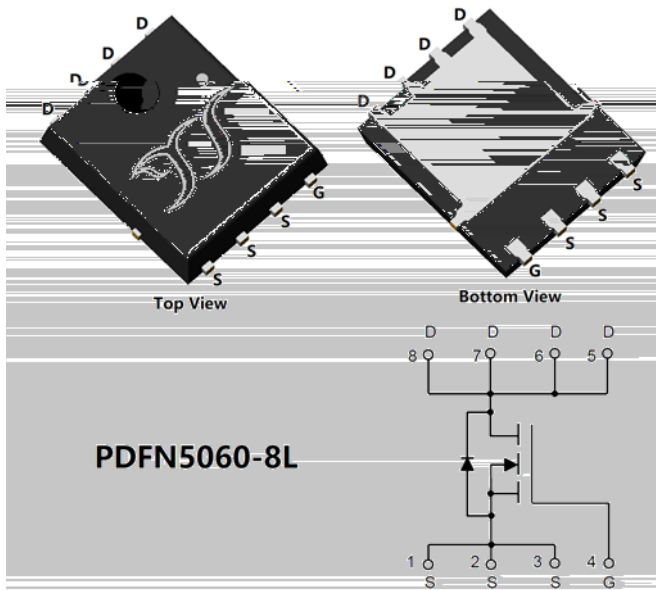


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	100V
I_D	90A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	5.0mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	7.1mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split gate trench MOSFET technology
 Excellent package for heat dissipation
 High density cell design for low $R_{DS(ON)}$
 Moisture Sensitivity Level 1
 Epoxy Meets UL 94 V-0 Flammability Rating
 Epoxy Meets UL 94 V-0 Flammability Rating

Applications

Power switching application
 Hard switched and high frequency circuits
 Uninterruptible power supply

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	20	V
Drain Current	$T_C=25$	I_D	90	A
	$T_C=100$		57	
Pulsed Drain Current ^A		I_{DM}	360	A
Avalanche energy ^B		EAS	400	mJ
Total Power Dissipation ^C	$T_C=25$	P_D	120	W
	$T_C=100$		48	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	t 10S	R	15	20	/W
	Steady-State		40	50	
Thermal Resistance Junction-to-Case	Steady-State	R	0.84	1.04	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG90G10A	F1	YJG90G10A	5000	10000	100000	13 reel



YJG90G10A

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	A

Gate-



YJG90G10A

Typical Performance Characteristics

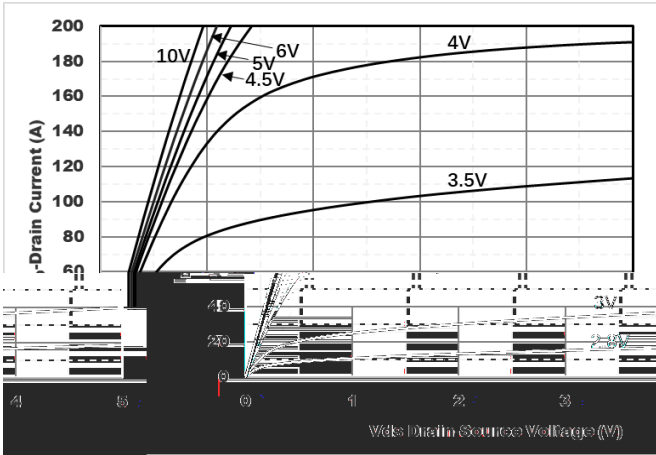


Figure1. Output Characteristics

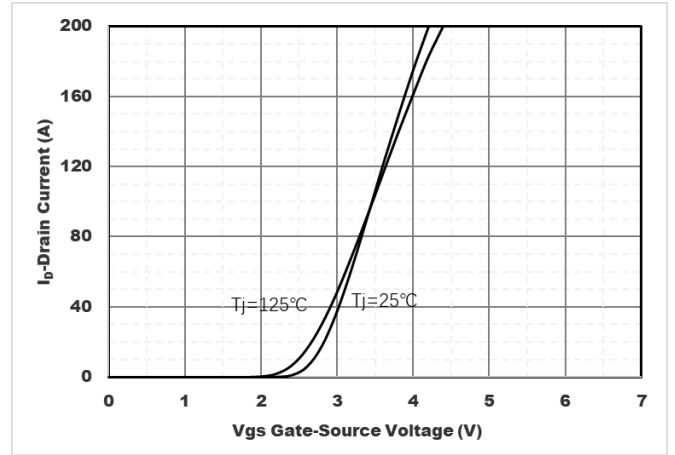


Figure2. Transfer Characteristics

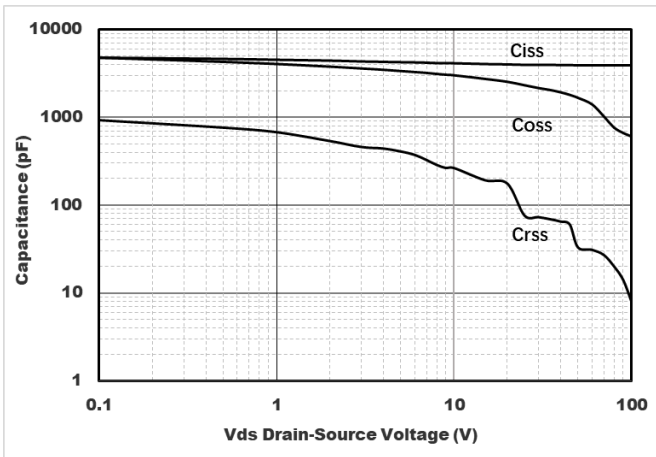


Figure3. Capacitance Characteristics

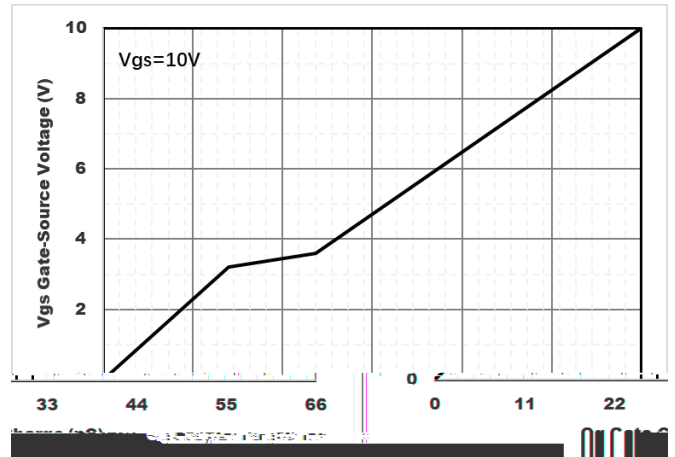


Figure4. Gate Charge

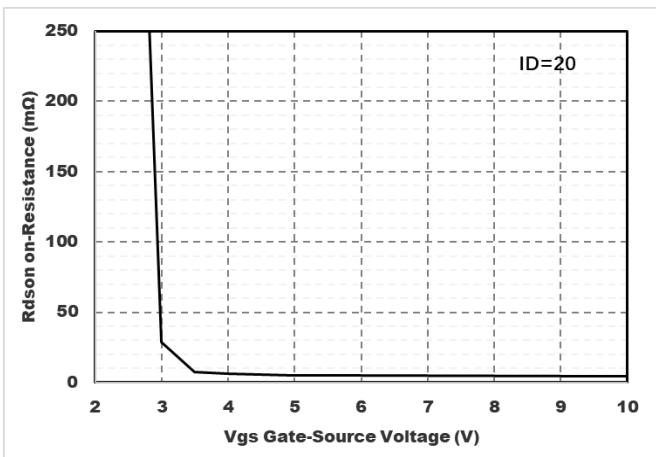


Figure5. : On-Resistance vs. Gate to Source Voltage

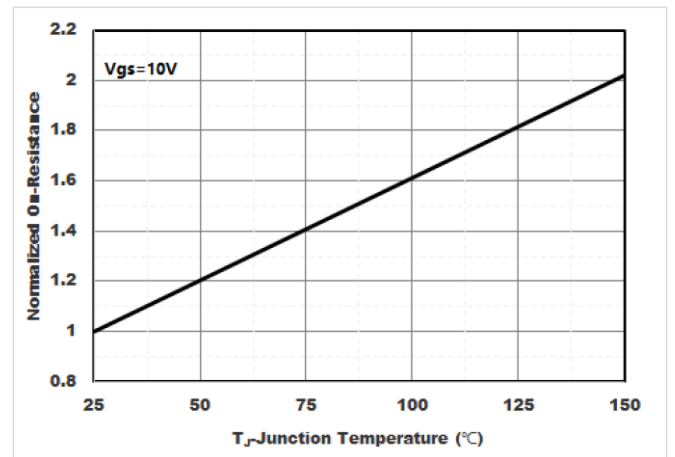


Figure6. Normalized On-Resistance



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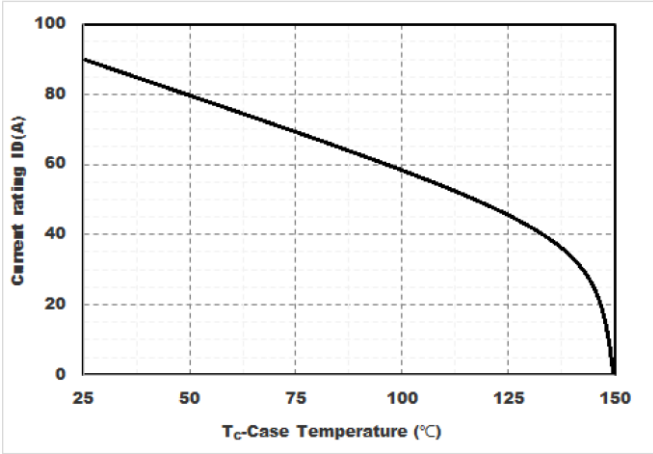


Figure7. Drain current

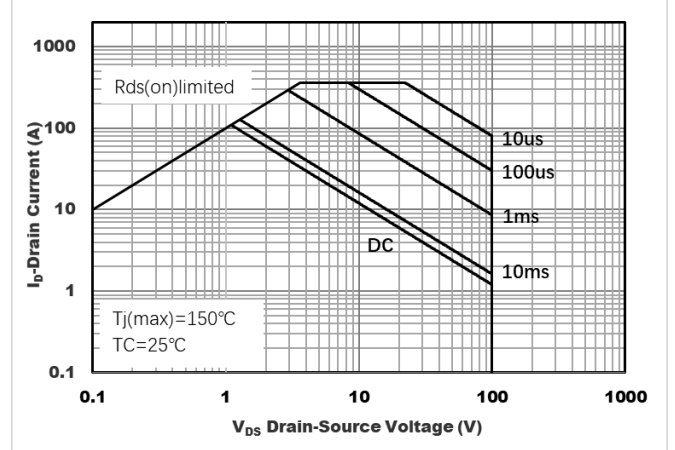


Figure8.Safe Operation Area

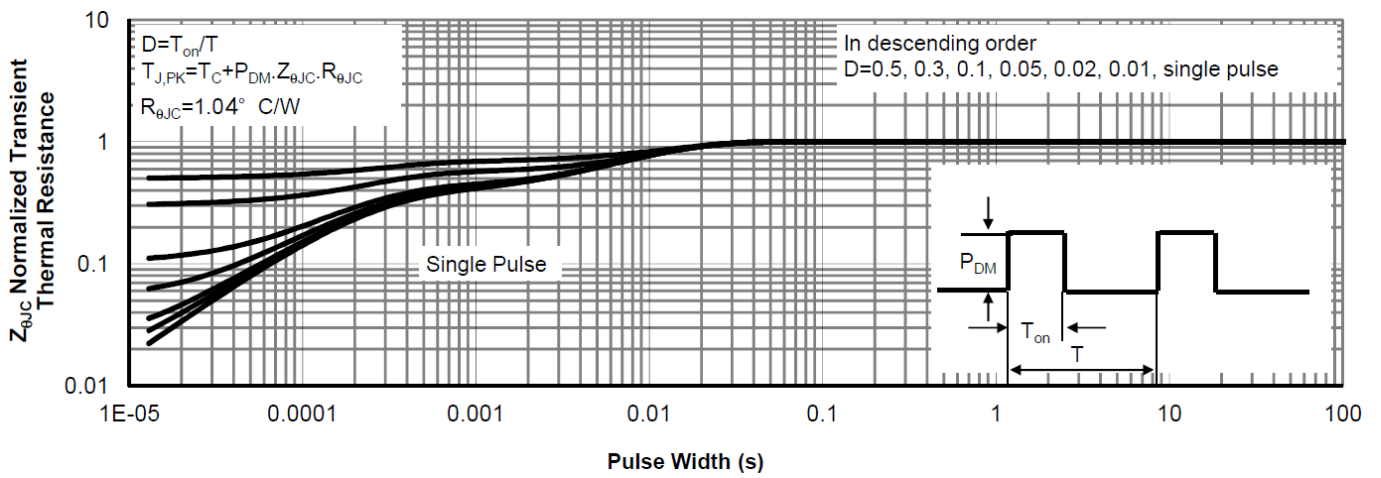
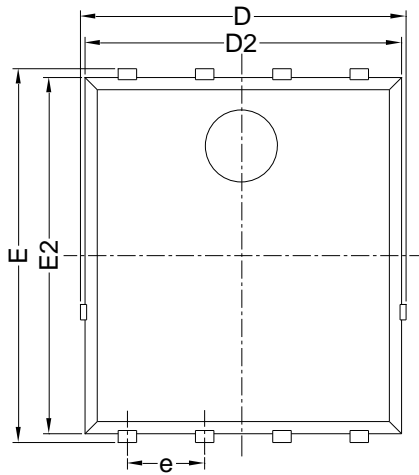


Figure9.Normalized Maximum Transient thermal impedance

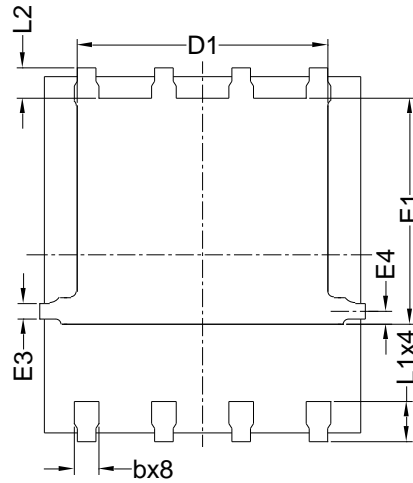


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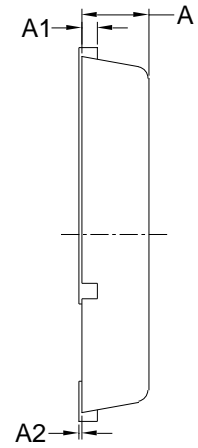
PDFN5060-8L-B-1.1MM Package information



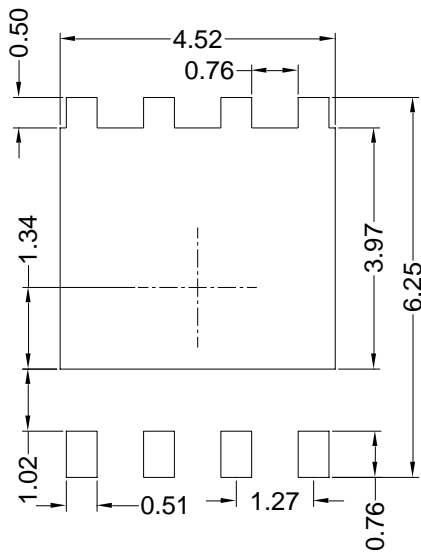
Top View



Bottom View



Side View



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



YJG90G10A

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